

Silicon NPN Power Transistors

2SC2830

DESCRIPTION

- With TO-3 package
- High voltage ,high speed
- Wide area of safe operation

APPLICATIONS

- For switching regulator applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

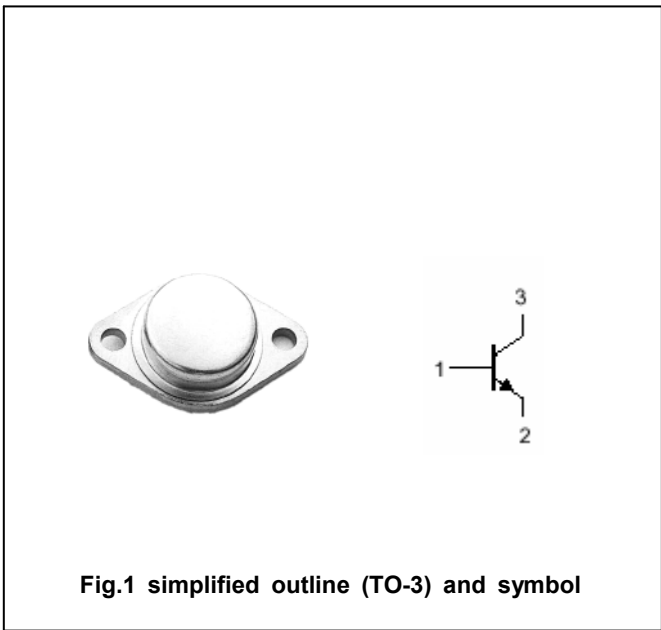


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		20	A
P <sub>T</sub>	Total power dissipation	T <sub>mb</sub> =25°C	200	W
T <sub>j</sub>	Junction temperature		200	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-mb</sub>	Thermal resistance from junction to mounting base	1.0	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =12A; I <sub>B</sub> =2.4A			1.2	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =12A; I <sub>B</sub> =2.4A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =500V; I <sub>E</sub> =0			0.1	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =400V; I <sub>B</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =2.4A ; V <sub>CE</sub> =5V	15		50	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =12A ; V <sub>CE</sub> =5V	10			

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PACKAGE OUTLINE

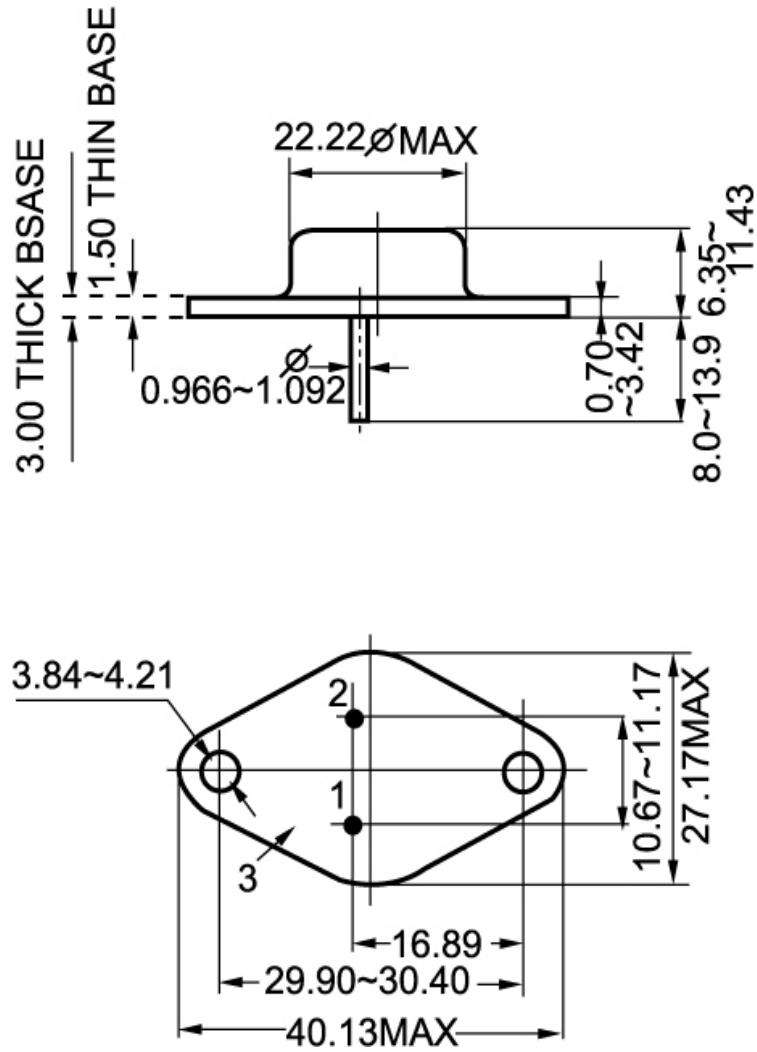


Fig.2 Outline dimensions